

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICELIST OF REFERENCES CITED BY APPLICANT(S)
(Use several sheets if necessary)ATTY DOCKET NO.
35.C10530C/D2APPLICATION NO.
Div. of 08/863,717APPLICANT
KIYOFUMI SAKAGUCHI, ET AL.FILING DATE
September 29, 1998GROUP
NYA

8823

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
G	5466631	11/95	Ichikawa, et al.	—	—	
G	5453394	9/95	Yonehara, et al.	—	—	
G	5277748	1/94	Sakaguchi, et al.	—	—	
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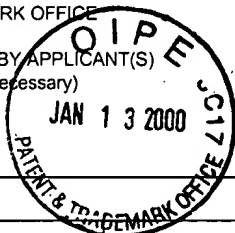
EXAMINER

FOURSON

DATE CONSIDERED

4/30/01

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ATTY DOCKET NO. 35.C10530C/D2

APPLICATION NO.
09/161,774

APPLICANT...KIYOFUMI SAKAGUCHI ET AL.

FILING DATE September 29, 1998

GROUP 2823

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